New Understanding of Photoelectron Diffraction: Experiment

Gerd Schönhense

Institute of Physics, Johannes Gutenberg University, Staudingerweg 7, 55128 Mainz, Germany

Email: schoenhe@uni-mainz.de

Abstract. Photoelectron diffraction (PED), which was first developed in the 1970s [1,2], has become a powerful technique for analysing the structure of solids. Recording efficiency has been greatly improved by a full-field imaging approach, and extending into the hard X-ray region provides access to true bulk information [3]. In this study, we present a novel application of PED at extremely low kinetic energies, within the range of the minimum inelastic mean free path curve [4]. Measurements were performed at beamline I09 of the Diamond Light Source (Harwell Campus, UK). The soft X-ray branch houses a unique momentum microscope that combines a large hemispherical analyser with time-of-flight detection. This allows the simultaneous acquisition of I(E_B,k_x,k_y) data arrays [5].

A full-field PED pattern with a diameter of ~7 Å⁻¹ is typically acquired in 5-10 minutes. This high recording speed enables **PED movies** to be captured with small kinetic energy steps down to 2 eV. Such movies have been recorded for Si 2p, Ge 3d and Ge 3p core-level photoelectrons at final state energies between 45 and 400 eV (kinetic energy <u>inside</u> the material). Thanks to a novel type of objective lens [6], these patterns correspond to polar angle ranges of 0-90° at 45 eV and 0-30° at 230 eV. The richness in detail is incompatible with the low IMFP in this energy range. Fig. 1 shows different sections through such a 3D stack for Si $2p_{3/2}$; the image contrast is CDAD. Understanding these patterns requires new concepts to describe the core-level photoemission process, particularly with regard to the nature of the final state (see the talk by Jan Minar).

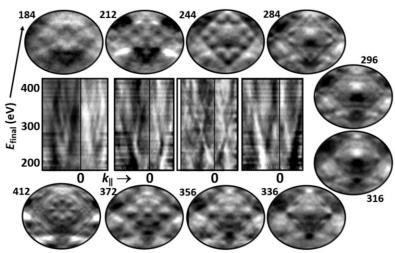


Figure 1. PED measurement (CDAD contrast) for Si $2p_{3/2}$, recorded in a photon energy range from 270 to 500 eV. The outer panels show k_x - k_y sections, the inner ones E_B -vs- $k_{parallel}$ sections at different positions. E_{final} = hv- E_B + V_0 is the kinetic energy inside of the solid. (from [7])

References:

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